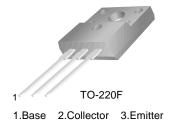


KSB1017

Power Amplifier Applications

Complement to KSD1408



PNP Silicon Epitaxial Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	- 80	V
V _{CEO}	Collector-Emitter Voltage	- 80	V
V _{EBO}	Emitter-Base Voltage	- 5	V
I _C	Collector Current	- 4	А
I _B	Base Current	- 0.4	А
P _C	Collector Dissipation (T _C =25°C)	25	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -50 \text{mA}, I_B = 0$	-80			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = -80V, I_{E} = 0$			- 30	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 100	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = -5V, I_{C} = -0.5A$ $V_{CE} = -5V, I_{C} = -3A$	40 15		240	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = -3A, I_B = -0.3A$		- 1	- 1.7	V
V _{BE} (on)	Base-Emitter ON Voltage	$V_{CE} = -5V, I_{C} = -3A$		- 1	- 1.5	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -5V, I_{C} = -0.5A$		9		MHz
C _{ob}	Output Capacitance	V _{CB} = - 10V, f = 1MHz		130		pF

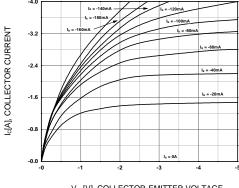
h_{FE} Classification

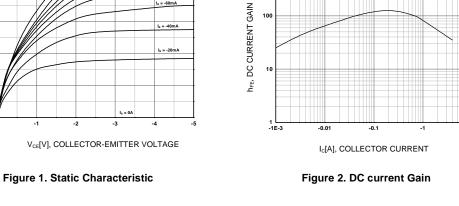
Classification	R	0	Y
h _{FE1}	40 ~ 80	70 ~ 140	120 ~ 240

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V_{CE} = -5V

Typical Characteristics





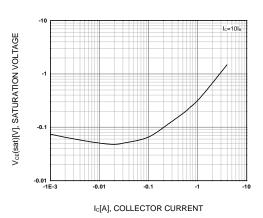


Figure 3. Collector-Emitter Saturation Voltage

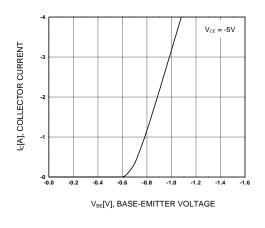


Figure 4. Base-Emitter On Voltage

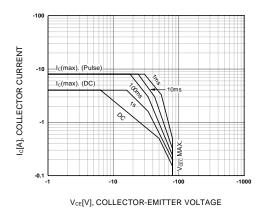


Figure 5. Safe Operating Area

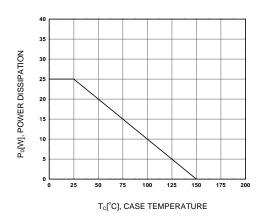
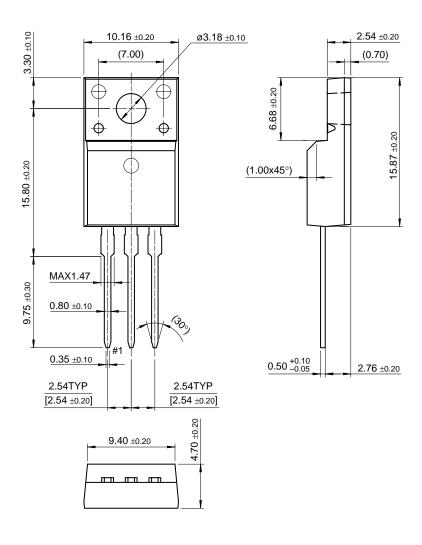


Figure 6. Power Derating

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Package Demensions

TO-220F



Dimensions in Millimeters

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